BLS6G3135-120; BLS6G3135S-120 LDMOS S-Band radar power transistor

Rev. 3 — 1 September 2015



Product profile 1.

General description 1.1

120 W LDMOS power transistor intended for radar applications in the 3.1 GHz to 3.5 GHz range.

Table 1. **Typical performance**

Typical RF performance at $T_{case} = 25$ °C; $t_p = 300 \ \mu s$; $\delta = 10 \ \%$; $I_{Dq} = 100 \ mA$; in a class-AB production test circuit.

Mode of operation	f	V _{DS}	P _L	G _p	η _D	t _r	t _f
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	3.1 to 3.5	32	120	11	43	20	6

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Typical pulsed RF performance at a frequency of 3.1 GHz to 3.5 GHz, a supply voltage of 32 V, an I_{Da} of 100 mA, a t_p of up to 300 μ s with δ of 10 %:
 - Output power = 120 W
 - Gain = 11 dB
 - Efficiency = 43 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (3.1 GHz to 3.5 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 S-Band power amplifiers for radar applications in the 3.1 GHz to 3.5 GHz frequency range

2. Pinning information

Pin	Description		Simplified outline	Symbol
BLS6G31	35-120 (SOT502A)			
1	drain			
2	gate			1 لــــا
3	source	<u>[1]</u>	-2	
				3 sym112
				Symme
	35S-120 (SOT502B)			
1	drain			4
2	gate			نـــار
3	source	<u>[1]</u>		2
				3
				sym112

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BLS6G3135-120	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLS6G3135S-120	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,		
Symbol	Parameter	Min	Max	Unit
V _{DS}	drain-source voltage	-	60	V
V _{GS}	gate-source voltage	-0.5	+13	V
I _D	drain current	-	7.2	А
T _{stg}	storage temperature	-65	+150	°C
Tj	junction temperature	-	225	°C

5. Thermal characteristics

Table 5.	Thermal characteristics				
Symbol	Parameter	Conditions	Тур	Max	Unit
Z _{th(j-mb)}	,	T _{case} = 85 °C; P _L = 120 W			
junction to mounting base	junction to mounting base	t_p = 300 μ s; δ = 10 %	0.29	0.40	K/W
		t_p = 100 μ s; δ = 20 %	0.30	0.41	K/W

6. Characteristics

Table 6. Characteristics

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

Parameter	Conditions	Min	Тур	Мах	Unit
drain-source breakdown voltage	V_{GS} = 0 V; I _D = 0.5 mA	60	-	-	V
gate-source threshold voltage	V _{DS} = 10 V; I _D = 180 mA	1.4	1.8	2.3	V
drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	5	μA
drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	27	33	-	A
gate leakage current	V_{GS} = 8.3 V; V_{DS} = 0 V	-	-	450	nA
forward transconductance	V _{DS} = 10 V; I _D = 9 A	-	13	-	S
drain-source on-state resistance	V _{GS} = V _{GS(th)} + 3.75 V; I _D = 6.3 A	-	0.085	0.160	Ω
	drain-source breakdown voltage gate-source threshold voltage drain leakage current drain cut-off current gate leakage current forward transconductance drain-source on-state	drain-source breakdown voltage $V_{GS} = 0 \text{ V}; \text{ I}_D = 0.5 \text{ mA}$ gate-source threshold voltage $V_{DS} = 10 \text{ V}; \text{ I}_D = 180 \text{ mA}$ drain leakage current $V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}$ drain cut-off current $V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}$ gate leakage current $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$ gate leakage current $V_{GS} = 8.3 \text{ V}; \text{ V}_{DS} = 0 \text{ V}$ forward transconductance $V_{DS} = 10 \text{ V}; \text{ I}_D = 9 \text{ A}$ drain-source on-state $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$	drain-source breakdown voltage $V_{GS} = 0 \text{ V}; \text{ I}_D = 0.5 \text{ mA}$ 60gate-source threshold voltage $V_{DS} = 10 \text{ V}; \text{ I}_D = 180 \text{ mA}$ 1.4drain leakage current $V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}$ -drain cut-off current $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$ 27gate leakage current $V_{GS} = 8.3 \text{ V}; \text{ V}_{DS} = 0 \text{ V}$ -forward transconductance $V_{DS} = 10 \text{ V}; \text{ I}_D = 9 \text{ A}$ -drain-source on-state $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ -	drain-source breakdown voltage $V_{GS} = 0 \text{ V}; \text{ I}_D = 0.5 \text{ mA}$ 60 - gate-source threshold voltage $V_{DS} = 10 \text{ V}; \text{ I}_D = 180 \text{ mA}$ 1.4 1.8 drain leakage current $V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}$ - - drain cut-off current $V_{GS} = V_{GS(th)} + 3.75 \text{ V}; \\V_{DS} = 10 \text{ V}$ 27 33 gate leakage current $V_{GS} = 8.3 \text{ V}; \text{ V}_{DS} = 0 \text{ V}$ - - forward transconductance $V_{DS} = 10 \text{ V}; \text{ I}_D = 9 \text{ A}$ - 13 drain-source on-state $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ - 0.085	drain-source breakdown voltage $V_{GS} = 0 \text{ V}; \text{ I}_D = 0.5 \text{ mA}$ 60gate-source threshold voltage $V_{DS} = 10 \text{ V}; \text{ I}_D = 180 \text{ mA}$ 1.41.82.3drain leakage current $V_{GS} = 0 \text{ V}; \text{ V}_{DS} = 28 \text{ V}$ 5drain cut-off current $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ 2733-gate leakage current $V_{GS} = 8.3 \text{ V}; \text{ V}_{DS} = 0 \text{ V}$ -450forward transconductance $V_{DS} = 10 \text{ V}; \text{ I}_D = 9 \text{ A}$ -13-drain-source on-state $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ -0.0850.160

7. Application information

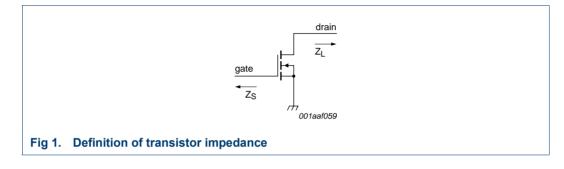
Table 7.Application information

Mode of operation: pulsed RF; $t_p = 300 \ \mu s$; $\delta = 10 \ \%$; RF performance at $V_{DS} = 32 \ V$; $I_{Dq} = 100 \ mA$; $T_{case} = 25 \ C$; unless otherwise specified, in a class-AB production circuit.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
PL	output power		-	120	-	W
V _{CC}	supply voltage	P _L = 120 W	-	-	32	V
G _p	power gain	P _L = 120 W	9.5	11	-	dB
IRL	input return loss	P _L = 120 W	6	10	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	P _L = 120 W	-	130	-	W
η_D	drain efficiency	P _L = 120 W	39	43	-	%
t _r	rise time	P _L = 120 W	-	20	50	ns
t _f	fall time	P _L = 120 W	-	6	50	ns

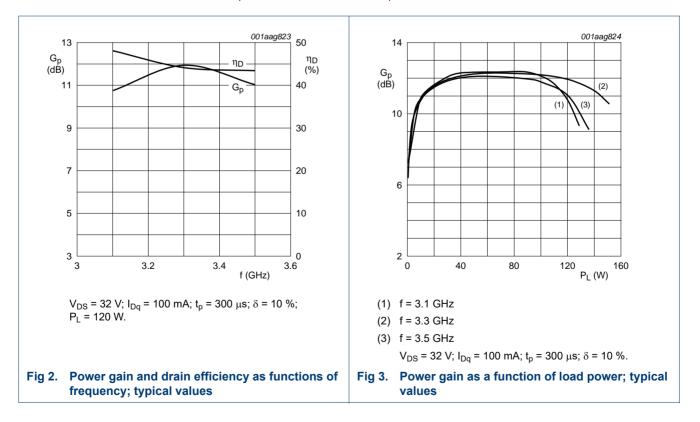
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Table 8.	Typical impedance		
f	Zs	3	ZL
GHz	Ω		Ω
3.1	2.1	7 – j5.4	5.9 – j5.9
3.2	3.3	3 – j4.7	4.5 – j6.2
3.3	4.2	2 – j4.4	3.5 - j6.0
3.4	5.2	2 – j4.8	2.7 – j5.6
3.5	5.	7 – j6.2	2.0 – j5.2



7.1 Ruggedness in class-AB operation

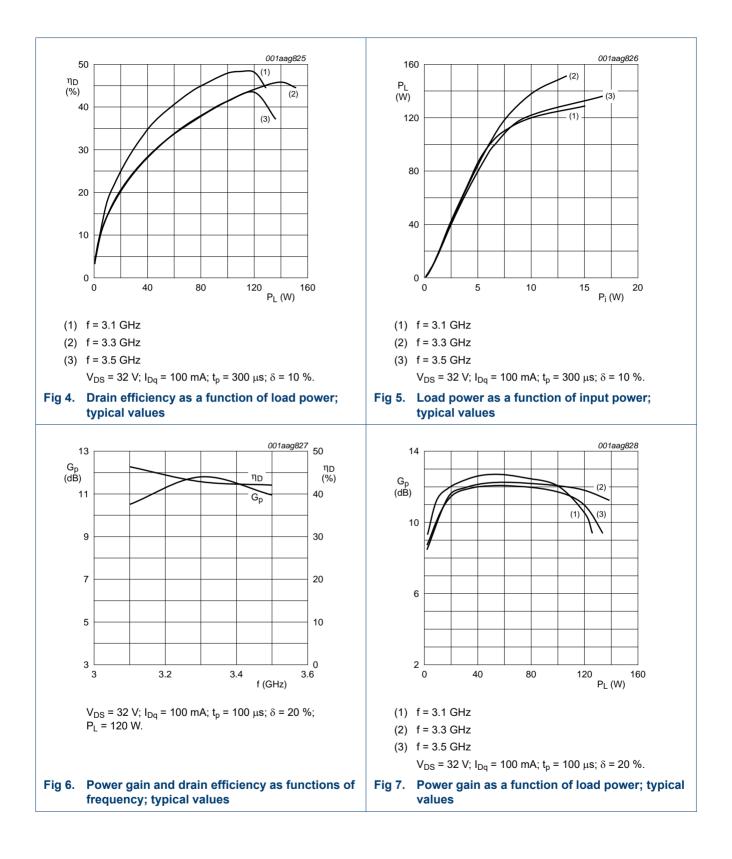
The BLS6G3135-120 and BLS6G3135S-120 are capable of withstanding a load mismatch corresponding to VSWR = 5 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Da} = 100 mA; P_L = 120 W; t_p = 300 μ s; δ = 10 %.



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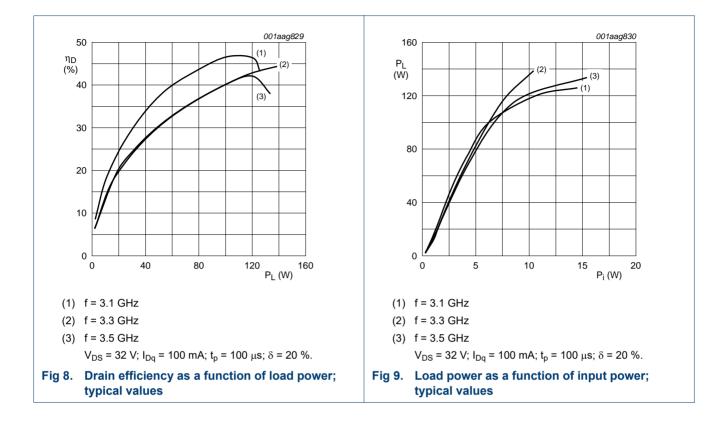
BLS6G3135-120; BLS6G3135S-120

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BLS6G3135-120; BLS6G3135S-120

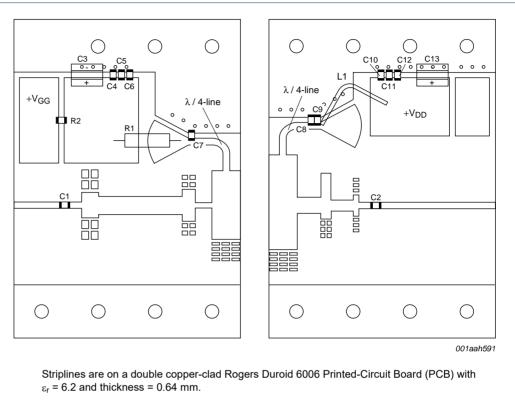
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8. Test information



See Table 9 for list of components.

Fig 10. Component layout for 3.1 GHz to 3.5 GHz MHz test circuit

Table 9. List of components (see Figure 10)

To ensure good power supply of the device, adding an electrolytical capacitor close to the supply connection of the circuit may be required. The actual capacitor value may differ depending on the pulse format, the quality of the power supply and the length of the connecting wires to the power supply. In general a value of 470 µF will be sufficient.

C1, C2, C4, C5, C6, C7, C8, C9, C11 C3	multilayer ceramic chip capacitor	24 pF	<u>[1]</u>
C3			
03	electrolytic capacitor	20 μF; 20 V	
C10	multilayer ceramic chip capacitor	33 pF	[1]
C12	multilayer ceramic chip capacitor	1 nF	[2]
C13	electrolytic capacitor	100 μF; 63 V	
L1	copper wire	-	
R1	resistor	49.9 Ω	
R2	SMD resistor	49.9 Ω	

[1] American Technical Ceramics type 100A or capacitor of same quality.

[2] American Technical Ceramics type 700A or capacitor of same quality.

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9. Package outline

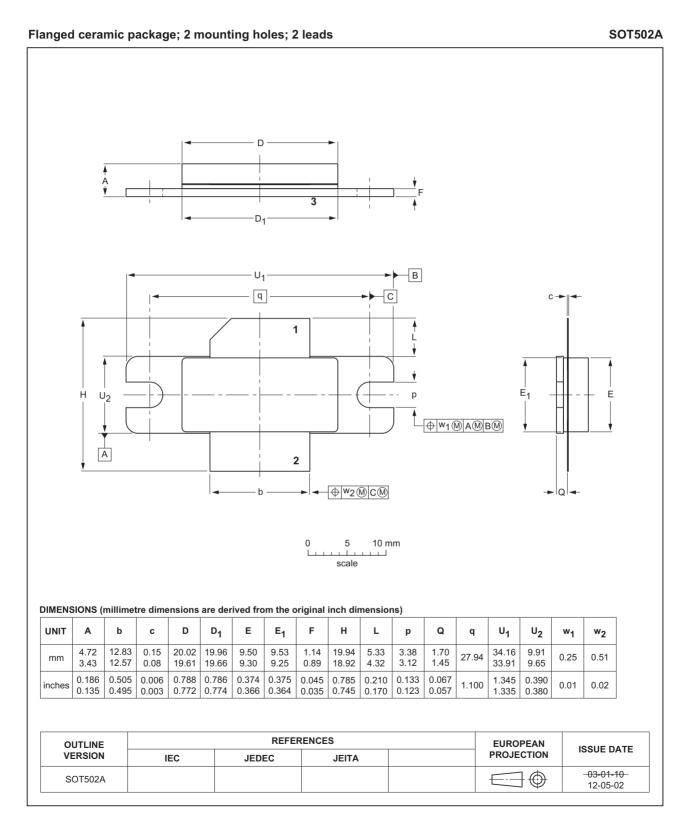


Fig 11. Package outline SOT502A

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Earless flanged ceramic package; 2 leads

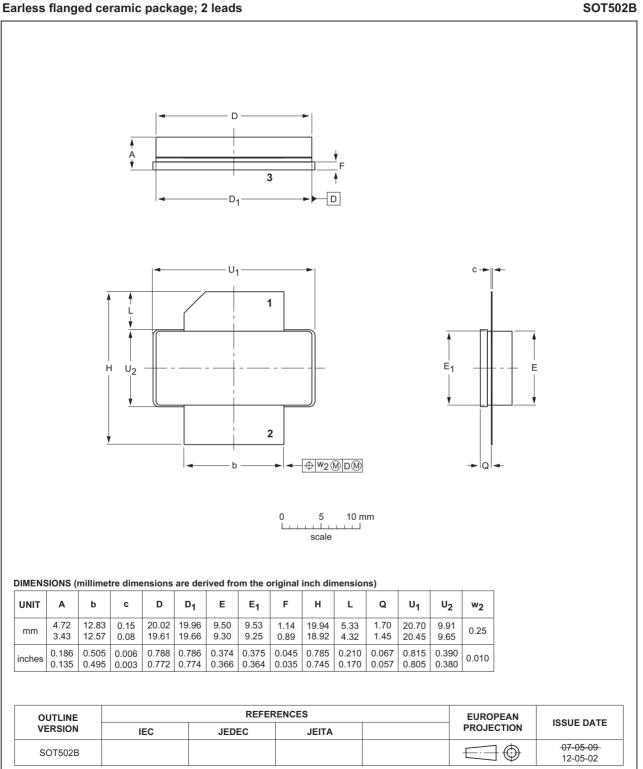


Fig 12. Package outline SOT502B

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Product data sheet

LDMOS S-Band radar power transistor

10. Abbreviations

Table 10.	Abbreviations
Acronym	Description
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Lateral Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
S-Band	Short wave Band
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLS6G3135-120_6G3135S-120#3	20150901	Product data sheet		BLS6G3135-120_6G3135S -120#2	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLS6G3135-120_6G3135S-120#2	20080529	Product data sheet	-	BLS6G3135-120_6G3135S -120#1	
BLS6G3135-120_6G3135S-120#1	20070814	Preliminary data sheet	-	-	

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12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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